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Dated: July 21, 2005

Signature

(Lawrence E. Russ)

Docket No.: EMCORE 3.0-084
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Pophristic et al.

Application No.: 10/780,526

Group Art Unit: 2811

Filed: February 17, 2004

Examiner: Not Yet
Assigned

For: LOW DOPED LAYER FOR NITRIDE-
BASED SEMICONDUCTOR DEVICE

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

It is respectfully requested that the references listed on the enclosed form be made of record and considered with respect to the above-referenced U.S. patent application. A copy of each foreign and non-patent literature reference is enclosed. Also enclosed is a copy of a communication from a foreign patent office in a counterpart foreign application to the above-referenced patent application which first cited the listed references. Submission of the present Information Disclosure Statement should not be taken as an admission that the cited references are legally available prior art or that the same are pertinent or material.

In the event that any fee is due in connection with the present Information Disclosure Statement, the Commissioner is

hereby authorized to charge the same to our Deposit Account No.
12-1095.

Dated: July 21, 2005

Respectfully submitted,

By 
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CERTIFICATION PURSUANT TO 37 C.F.R. § 1.97(e) (1)

Dear Sir:

Pursuant to 37 C.F.R. § 1.97(e) (1), undersigned counsel hereby certifies that each item of information contained in the accompanying Information Disclosure Statement was first cited in a communication from a foreign patent office in a counterpart foreign application to the above-referenced patent application not more than three months prior to the filing of said statement.

Dated: July 21, 2005

Respectfully submitted,

By *Lawrence E. Russ*

Lawrence E. Russ

Registration No.: 35,342

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Substitute for form 1449A/B/PTO				Complete if Known	
				Application Number	10/780,526
				Filing Date	February 17, 2004
				First Named Inventor	Milan Pophristic
				Art Unit	2811
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	EMCORE 3.0-084

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
AA	US-2003/141518-A1	07-31-2003	Yokogawa et al.		
AB	US-5,296,395	03-22-1994	Khan et al.		
AC	US-6,653,215-B1	11-25-2003	Brown et al.		

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)			
BA	EP-1 189 287-A		03-20-2002	Matsushita Electric Industrial Co., Ltd.	
BB	WO-03/026021-A		03-27-2003	Cree Lighting Company	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹Applicant's unique citation designation number (optional). ²See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
	CA	"High barrier height GaN Schottky diodes: Pt/GaN and Pd/GaN" APPLIED PHYSICS LETTERS, AMERICAN INSTITUTE OF PHYSICS, New York, US, vol. 68 no. 9, 2-26-96; pp. 1267-1269			
	CB	Lin Yow-Jon et al: "Nitrogen-vacancy-related defects and Fermi level pinning in n-GaN Schottky diodes" 8/1/03, JOURNAL OF APPLIED PHYSICS, AMERICAN INSTITUTE OF PHYSICS, New York, US, pp. 1819-1822.			

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Examiner Signature	Date Considered
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